



### Description

The DMN2029USD uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

### General Features

$V_{DS} = 20V$   $I_D = 8A$

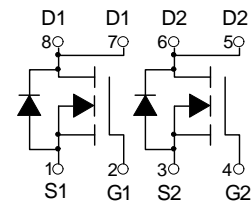
$R_{DS(ON)} < 20m\Omega$  @  $V_{GS}=4.5V$

### Application

Battery protection

Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN2029USD	SOP-8	HXY MOSFET	3000

### Absolute Maximum Ratings ( $T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	8	A
$I_{DM}$	Pulsed Drain Current	28	A
$P_D$	Maximum Power Dissipation	2.25	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	80	$^{\circ}C/W$



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	<b>BV<sub>DSS</sub></b>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	20	-	-	V
Gate Leakage Current	<b>I<sub>GSS</sub></b>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V	-	-	±100	nA
Drain Cut-off Current	<b>I<sub>DSS</sub></b>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	-	-	1	μA
Gate Threshold Voltage	<b>V<sub>GS(th)</sub></b>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250μA	0.45	0.7	1	V
Drain-Source On-State Resistance <sup>3</sup>	<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A	-	13	20	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4.7A	-	18	30	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 4.3A	-	28	57	
<b>Dynamic Characteristics<sup>4</sup></b>						
Input Capacitance	<b>C<sub>iSS</sub></b>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	<b>C<sub>oss</sub></b>		-	120	-	
Reverse Transfer Capacitance	<b>C<sub>rSS</sub></b>		-	105	-	
<b>Switching Characteristics<sup>4</sup></b>						
Total Gate Charge	<b>Q<sub>g</sub></b>	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A	-	10.5	-	nC
Gate-Source Charge	<b>Q<sub>gs</sub></b>		-	2	-	
Gate-Drain Charge	<b>Q<sub>gd</sub></b>		-	2.5	-	
Turn-On Time	<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 5V, V <sub>DD</sub> = 10V, I <sub>D</sub> = 5A, R <sub>G</sub> = 3Ω,	-	10	-	ns
Rise Time	<b>t<sub>r</sub></b>		-	20	-	
Turn-Off Time	<b>t<sub>d(off)</sub></b>		-	32	-	
Fall Time	<b>t<sub>f</sub></b>		-	12	-	
<b>Source-Drain Diode Characteristics</b>						
Body Diode Voltage <sup>3</sup>	<b>V<sub>SD</sub></b>	I <sub>S</sub> = 4A, V <sub>GS</sub> = 0V	-	-	1.2	V
Continuous Source Current	<b>I<sub>S</sub></b>		-	-	8	A

**Notes:**

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
4. This value is guaranteed by design hence it is not included in the production test.



### Typical Characteristics

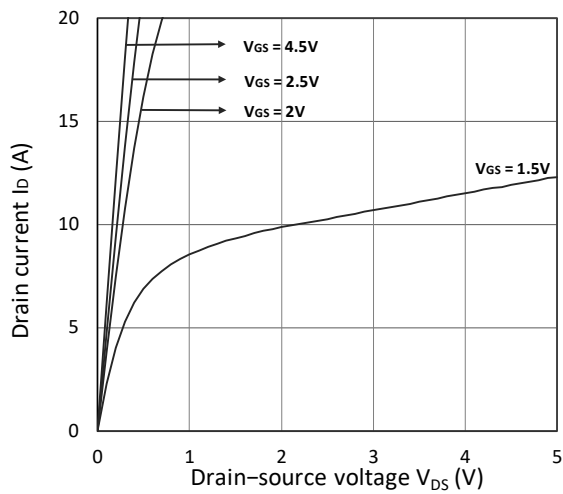


Figure 1. Output Characteristics

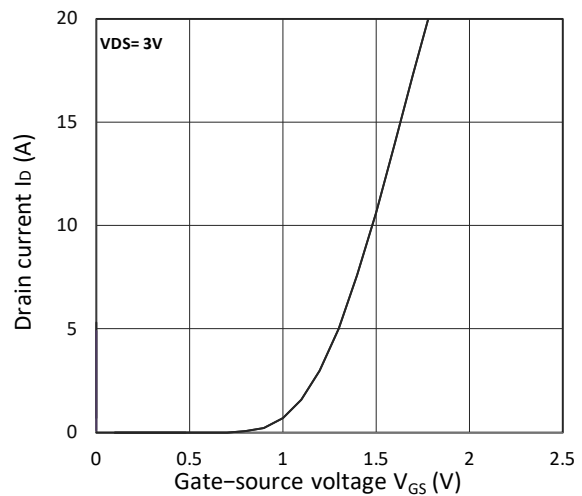


Figure 2. Transfer Characteristics

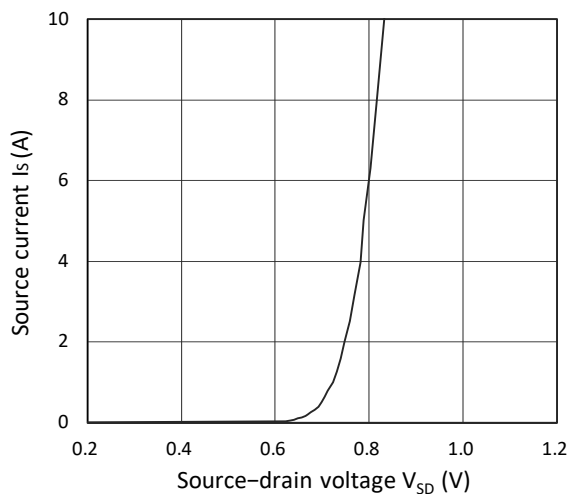


Figure 3. Forward Characteristics of Reverse

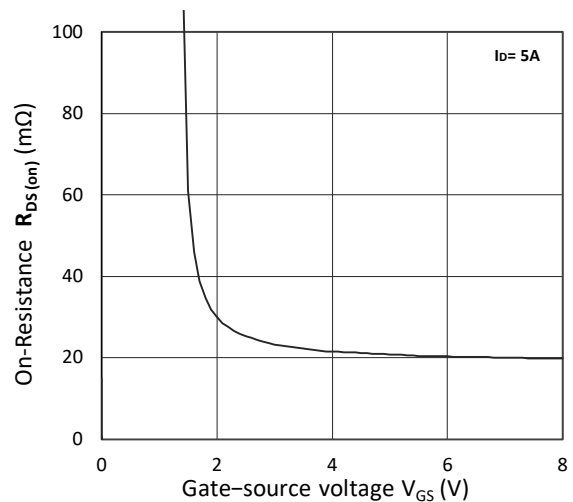


Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$

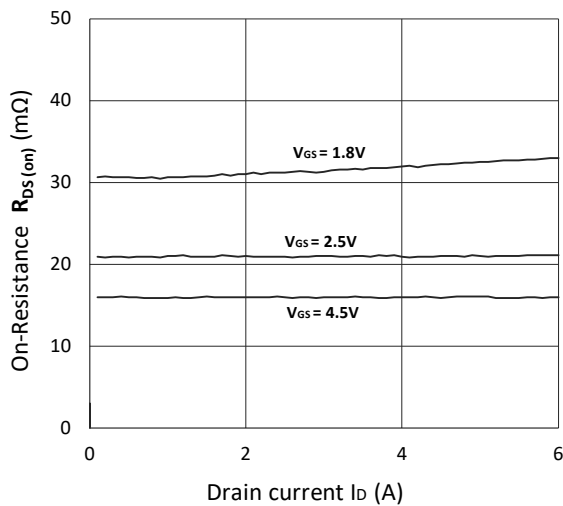


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$

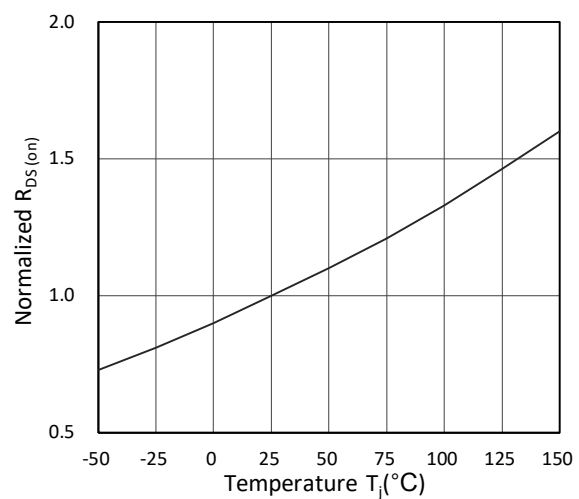


Figure 6. Normalized  $R_{DS(ON)}$  vs. Temperature

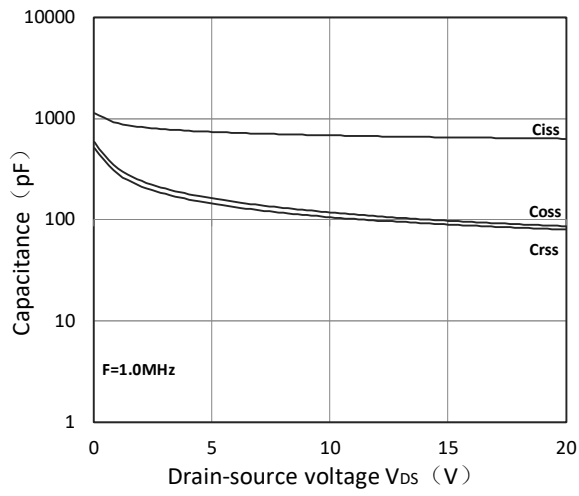


Figure 7. Capacitance Characteristics

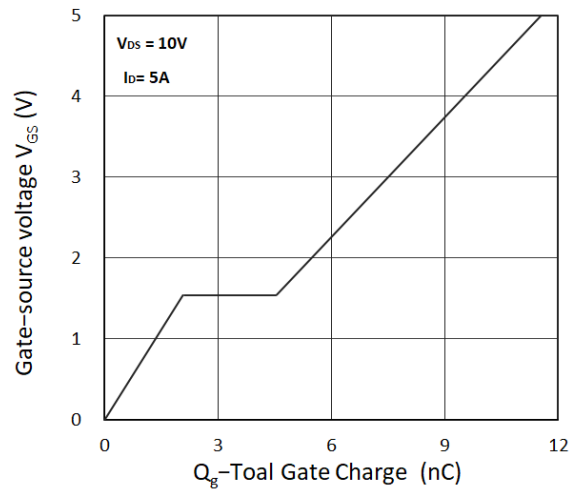
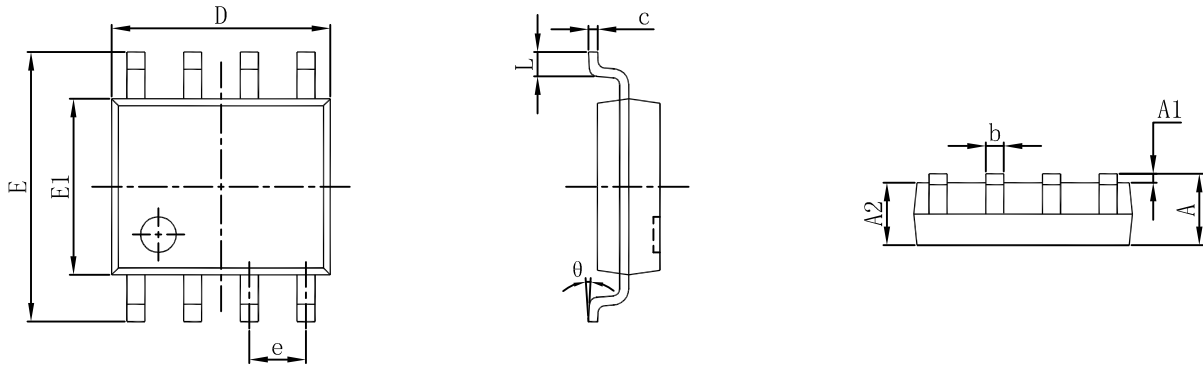


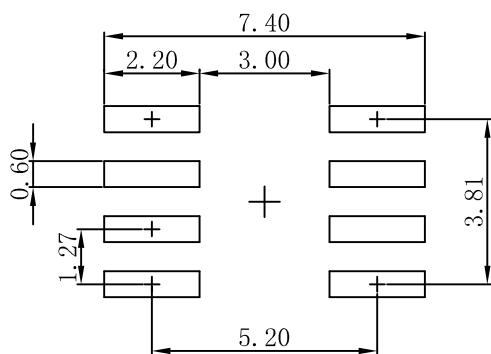
Figure 8. Gate Charge Characteristics



### SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.



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